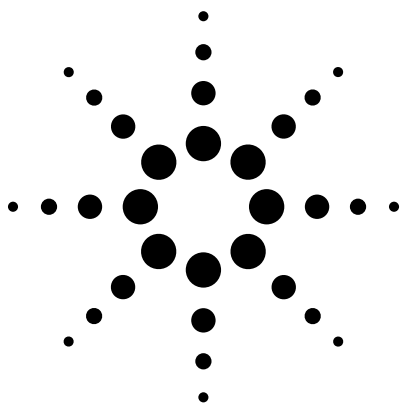




Agilent HCPL-814

AC Input Phototransistor

Optocoupler

High Density Mounting Type

Data Sheet

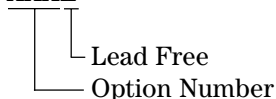
Description

The HCPL-814 contains a phototransistor, optically coupled to two light emitting diodes connected inverse parallel. It can operate directly by AC input current. It is packaged in a 4-pin DIP package and available in wide-lead spacing option and lead bend SMD option. Input-output isolation voltage is 5000 V_{rms}. Response time, t_r , is typically 4 μ s and minimum CTR is 20% at input current of ± 1 mA.

Ordering Information

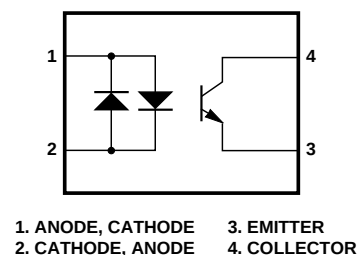
Specify Part Number followed by Option Number (if desired).

HCPL-814-XXxE



000 = No Options
 060 = IEC/EN/DIN EN 60747-5-2 Option
 W00 = 0.4" Lead Spacing Option
 300 = Lead Bend SMD Option
 500 = Tape and Reel Packaging Option
 00A = Rank Mark A

Functional Diagram



Features

- AC input response
- High input-output isolation voltage ($V_{iso} = 5,000 V_{rms}$)
- Low collector dark current (I_{CE0} : max. 10^{-7} A at $V_{CE} = 20$ V)
- Current transfer ratio (CTR: min. 20% at $I_F = \pm 1$ mA, $V_{CE} = 5$ V)
- Response time (t_r : typ. 4 μ s at $V_{CE} = 2$ V, $I_C = 2$ mA, $R_L = 100 \Omega$)
- Compact dual-in-line package
- UL approved
- CSA approved
- IEC/EN/DIN EN 60747-5-2 approved
- Options available:
 - Leads with 0.4" (10.16 mm) spacing (W00)
 - Leads bend for surface mounting (300)
 - Tape and reel for SMD (500)
 - IEC/EN/DIN EN 60747-5-2 approvals (060)

Applications

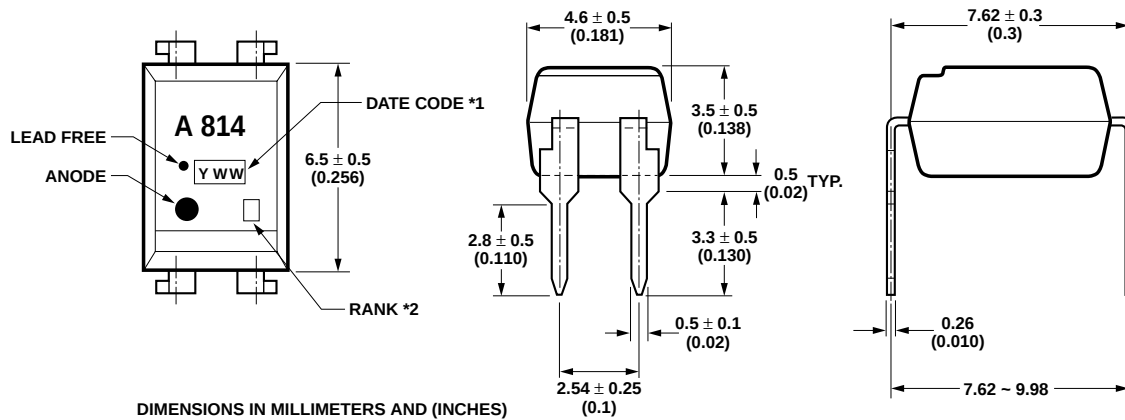
- Detecting or monitoring AC signals
- AC line/digital logic isolation
- Programmable logic controllers
- AC/DC – input modules

CAUTION: It is advised that normal static precautions be taken in handling and assembly of this component to prevent damage and/or degradation which may be induced by ESD.

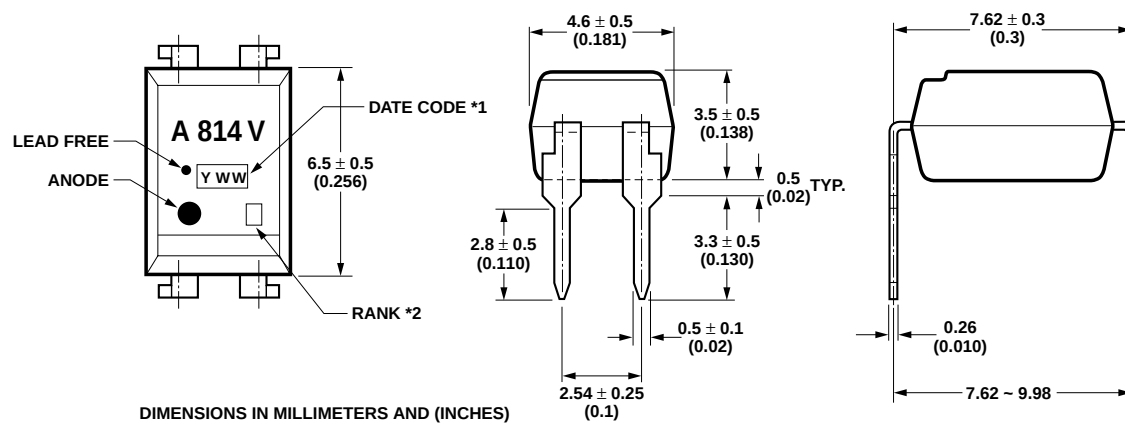


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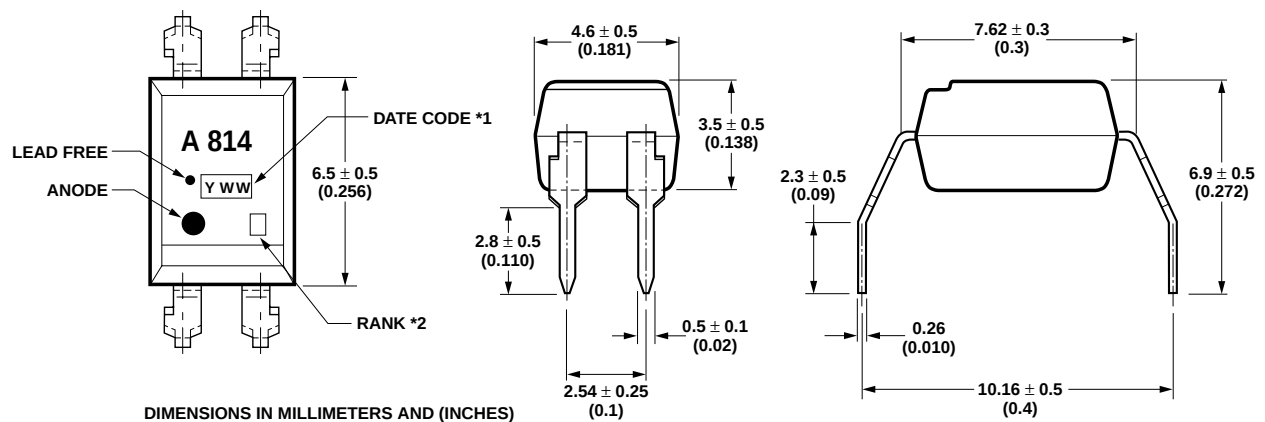
Package Outline Drawings
HCPL-814-000E



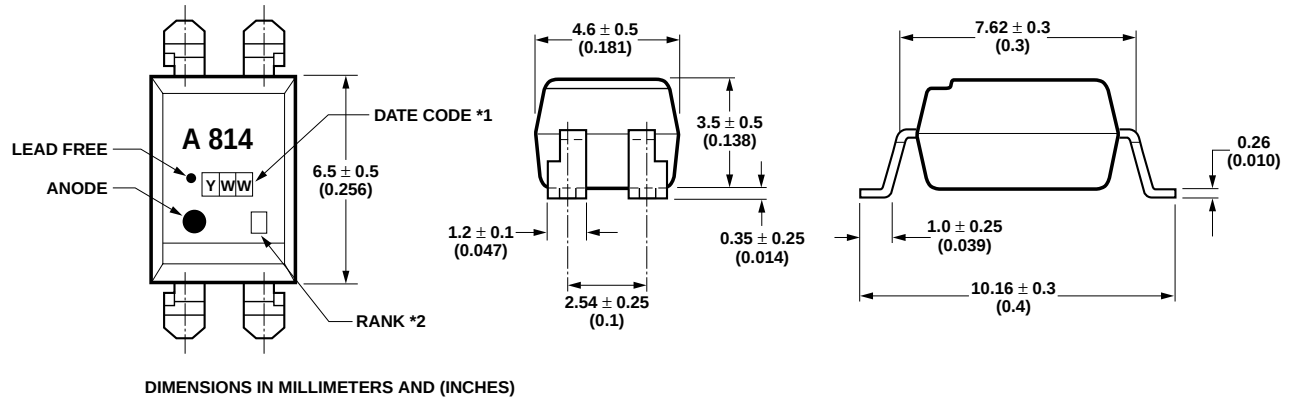
HCPL-814-060E



HCPL-814-W00E

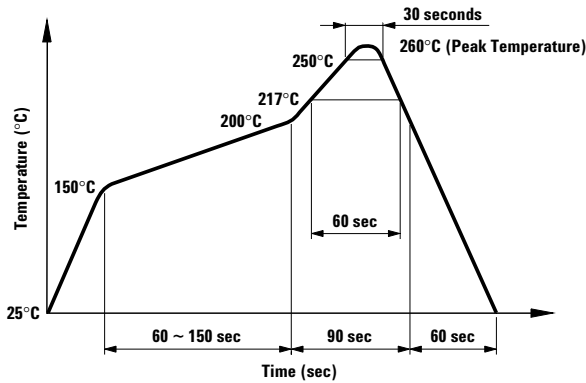


HCPL-814-300E



Solder Reflow Temperature Profile

- 1) One-time soldering reflow is recommended within the condition of temperature and time profile shown at right.
- 2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device. Keep the temperature on the package of the device within the condition of (1) above.



Absolute Maximum Ratings

Parameters	Symbol	Min.	Max.	Units
Storage Temperature	T _S	-55	125	°C
Ambient Operating Temperature	T _A	-30	100	°C
Lead Solder Temperature for 10s (1.6 mm below seating plane)	T _{sol}		260	°C
Average Forward Current	I _F		±50	mA
Input Power Dissipation	P _I		70	mW
Collector Current	I _C		50	mA
Collector-Emitter Voltage	V _{CE0}		35	V
Emitter-Collector Voltage	V _{EC0}		6	V
Collector Power Dissipation	P _C		150	mW
Total Power Dissipation	P _{tot}		200	mW
Isolation Voltage (AC for 1 minute, R.H. = 40 ~ 60%)[1]	V _{iso}		5000	V _{rms}

Electrical Specifications (T_A = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Forward Voltage	V _F	—	1.2	1.4	V	I _F = ±20 mA
Terminal Capacitance	C _t	—	50	250	pF	V = 0, f = 1 kHz
Collector Dark Current	I _{CEO}	—	—	100	nA	V _{CE} = 20 V, I _F = 0
Collector-Emitter Breakdown Voltage	BV _{CEO}	35	—	—	V	I _C = 0.1 mA, I _F = 0
Emitter-Collector Breakdown Voltage	BV _{ECO}	6	—	—	V	I _E = 10 μA, I _F = 0
Collector Current	I _C	0.2	—	3	mA	I _F = ±1 mA,
Current Transfer Ratio ^[2]	CTR	20	—	300	%	V _{CE} = 5 V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	0.1	0.2	V	I _F = ±20 mA, I _C = 1 mA
Isolation Resistance	R _{iso}	5 x 10 ¹⁰	1 x 10 ¹¹	—	Ω	DC 500 V 40 ~ 60% R.H.
Floating Capacitance	C _f	—	0.6	1	pF	V = 0, f = 1 MHz
Cut-off Frequency	f _c	15	80	—	kHz	V _{CE} = 5 V, I _C = 2 mA R _L = 100 Ω, -3 dB
Response Time (Rise)	t _r	—	4	18	μs	V _{CE} = 2 V, I _C = 2 mA,
Response Time (Fall)	t _f	—	3	18	μs	R _L = 100 Ω

Rank Mark	CTR (%)	Conditions
A	50 ~ 150	I _F = ±1 mA,
No Mark	20 ~ 300	V _{CE} = 5 V, T _A = 25°C

Notes:

- Isolation voltage shall be measured using the following method:
 - Short between anode and cathode on the primary side and between collector and emitter on the secondary side.
 - The isolation voltage tester with zero-cross circuit shall be used.
 - The waveform of applied voltage shall be a sine wave.

$$2. \text{CTR} = \frac{I_C}{I_F} \times 100\%$$

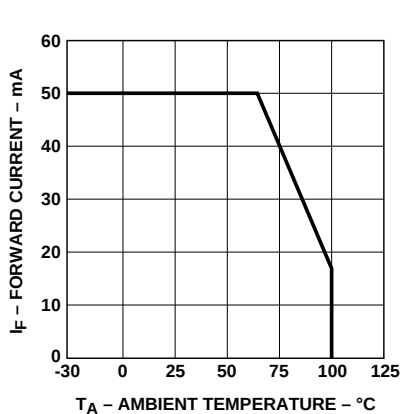


Figure 1. Forward current vs. temperature.

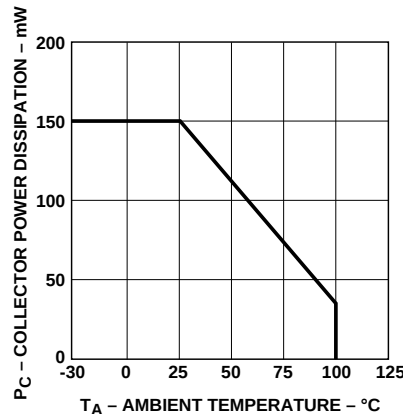


Figure 2. Collector power dissipation vs. temperature.

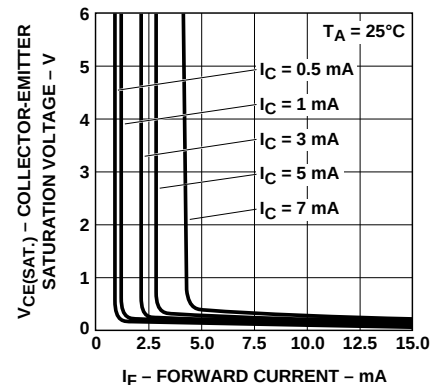


Figure 3. Collector-emitter saturation voltage vs. forward current.

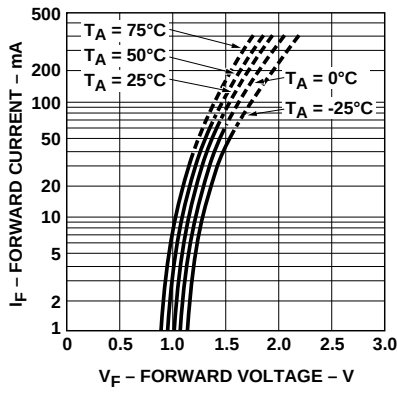


Figure 4. Forward current vs. forward voltage.

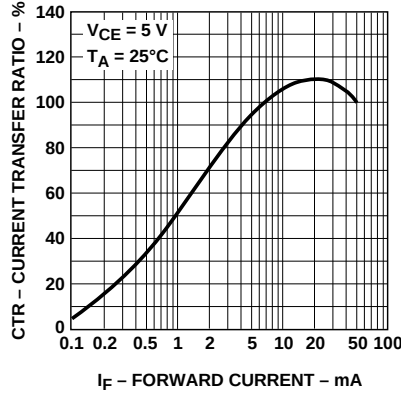


Figure 5. Current transfer ratio vs. forward current.

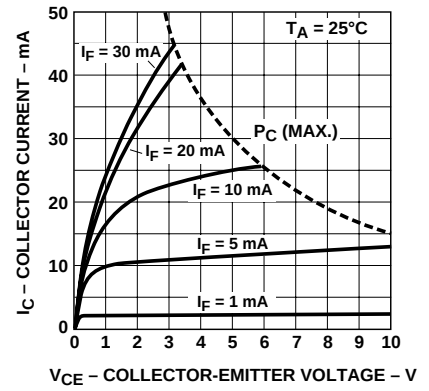


Figure 6. Collector current vs. collector-emitter voltage.

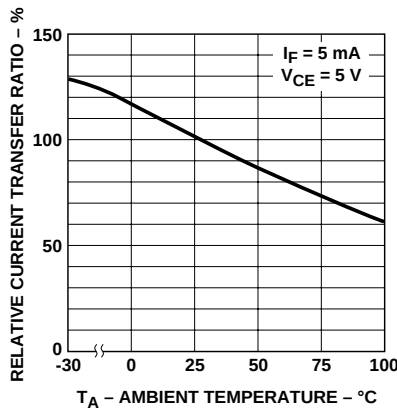


Figure 7. Relative current transfer ratio vs. temperature.

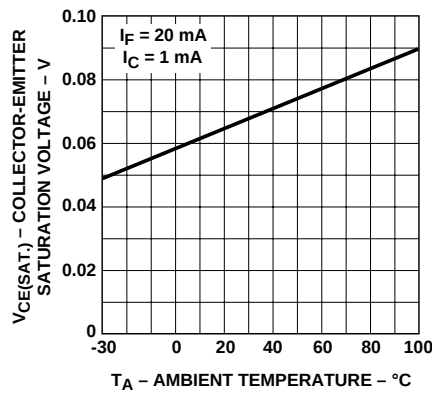


Figure 8. Collector-emitter saturation voltage vs. temperature.

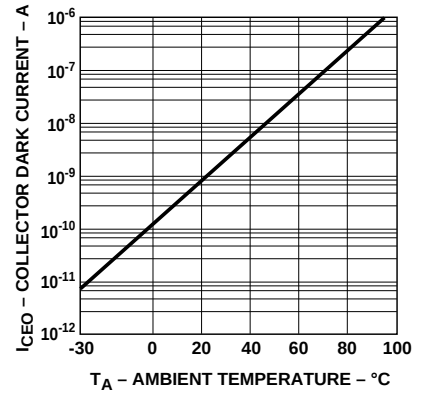


Figure 9. Collector dark current vs. temperature.

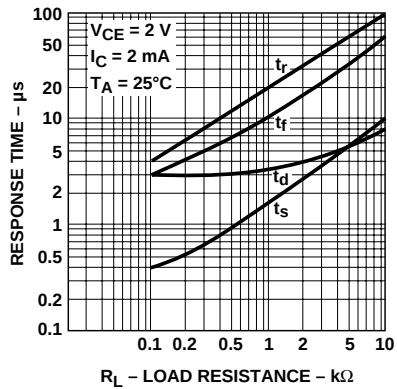


Figure 10. Response time vs. load resistance.

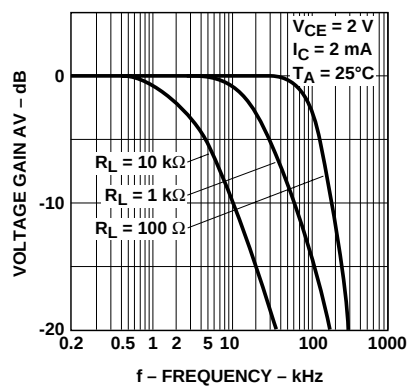


Figure 11. Frequency response.

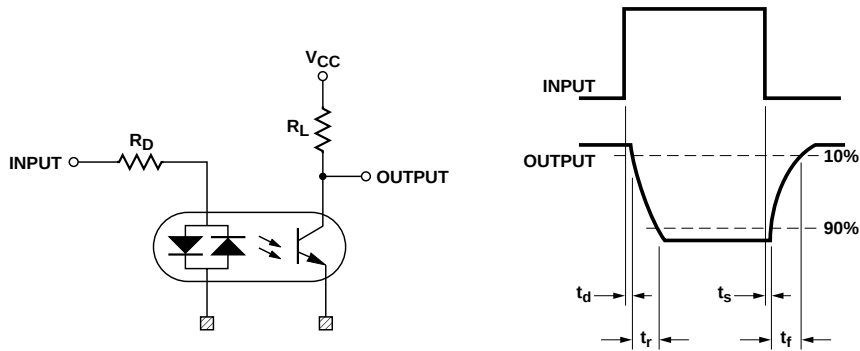


Figure 12. Test circuit for response time.

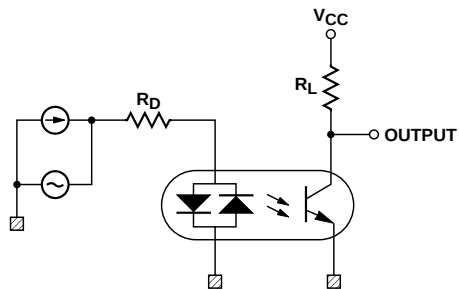


Figure 13. Test circuit for frequency response.

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Obsoletes 5989-0301EN

November 3, 2004

5989-1735EN



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